

Filed 11/12/1999

(2-92)

Sheet 1 of 1

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>			Docket Number (Optional) 2919.1US (98-0499.01)	Application Number 07/ To be assigned 072935		
			Applicant Pai-Hung Pan			
			Filing Date May 5, 1998	Group Art Unit Tente 2823 assigned		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	NAME	DATE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G	4,786,954	Morie et al.	11/22/88	—	—	
G	4,849,344	Desbiens et al.	07/18/89	—	—	
G	5,173,439	Dash et al.	12/22/92	—	—	
G	5,272,117	Roth et al.	12/21/93	—	—	
G	5,296,392	Grula et al.	03/22/94	—	—	
G	5,297,082	Lee	03/22/94	—	—	
G	5,346,587	Doan et al.	09/13/94	—	—	
G	5,433,794	Fazan et al.	07/18/95	—	—	
G	5,436,488	Poon et al.	07/25/95	—	—	
G	5,459,096	Venkatesan et al.	10/17/95	—	—	
G	5,492,858	Bose et al.	02/20/96	—	—	
G	5,516,625	McNamara et al.	05/14/96	—	—	
G	5,516,721	Galli et al.	05/14/96	—	—	
G	5,521,422	Mandelman et al.	05/28/96	—	—	
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						YES
OTHER DOCUMENTS <small>(Including Author, Title, Date, Pertinent Pages, Etc.)</small>						
G	Davari, et al., "A Variable-Size Shallow Trench Isolation (STI) Technology With Diffused Sidewall Doping For Submicron CMOS", IEEE IEDM (1988).					
G	K. Blumenstock et al., "Shallow Trench Isolation for Ultra-Large-Scale Integrated Devices", J. Vac. Sci. Technol., B 12(1) (Jan/Feb 1994).					
EXAMINER	DATE CONSIDERED					
FOURSON	11/21/99 7/25/06					
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						

IDS Filed 5/5/1998

as defined in 37 C.F.R. § 1.56(b). Further, no representation is made by Applicant herein that no other possible material information as defined in 37 C.F.R. § 1.56 (b) exists.

DOCUMENTS

U.S. Patent Documents

<u>U.S. Patent No.</u>	<u>Inventor</u>	<u>Issue Date</u>
4,786,954	Morie et al.	11/22/88
4,849,344	Desbiens et al.	07/18/89
5,173,439	Dash et al.	12/22/92
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5,433,794	Fazan et al.	07/18/95
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5,521,422	Mandelman et al.	05/28/96

Other Documents

G Davari, et al., "A Variable-Size Shallow Trench Isolation (STI) Technology With Diffused Sidewall Doping For Submicron CMOS", *IEEE IEDM* (1988).

G K. Blumenstock et al., "Shallow Trench Isolation for Ultra-Large-Scale Integrated Devices", *J. Vac. Sci. Technol.*, B 12(1) (Jan/Feb 1994).

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